

EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

Fast Thyristor Type **FDT56-1000-22**

Low switching losses
Distributed amplified gate for high di_T/dt

Mean on-state current				I_{TAV}	1000 A		
Repetitive peak off-state voltage				V_{DRM}	1400...2200 V		
Repetitive peak reverse voltage				V_{RRM}			
Turn-off time				t_q	20.0, 25.0, 32.0, 40.0 μs		
V_{DRM}, V_{RRM}, V	1400	1500	1600	1800	2000	2200	
Voltage code	14	15	16	18	20	22	
$T_j, ^\circ C$	-60...+125						

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	909 1000 1363	$T_c = 85^\circ C$; Double side cooled; $T_c = 79^\circ C$; Double side cooled; $T_c = 55^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	1570	$T_c = 79^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	22.0 25.0	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; $t_p = 10$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$; $V_G = 20$ V; $t_{GP} = 50$ μs ; $di_G/dt = 1$ A/ μs
			23.0 26.0	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; $t_p = 8.3$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$; $V_G = 20$ V; $t_{GP} = 50$ μs ; $di_G/dt = 1$ A/ μs
I^2t	Safety factor	$A^2s \cdot 10^3$	2400 3100	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; $t_p = 10$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$; $V_G = 20$ V; $t_{GP} = 50$ μs ; $di_G/dt = 1$ A/ μs
			2100 2800	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; $t_p = 8.3$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$; $V_G = 20$ V; $t_{GP} = 50$ μs ; $di_G/dt = 1$ A/ μs
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	1400...2200	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	1500...2300	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j = T_{jmax}$; Gate open	

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TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j = T_{j\max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	8	$T_j = T_{j\max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ μ s	2000	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 2800$ A; Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ μ s; $di_G/dt = 2$ A/ μ s
THERMAL				
T_{stg}	Storage temperature	$^{\circ}$ C	-60...+50	
T_j	Operating junction temperature	$^{\circ}$ C	-60...+125	
MECHANICAL				
F	Mounting force	kN	24.0...28.0	
a	Acceleration	m/s ²	50	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.35	$T_j = 25$ $^{\circ}$ C; $I_{TM} = 3140$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.397	$T_j = T_{j\max}$;	
r_T	On-state slope resistance, max	m Ω	0.313	$0.5 \pi I_{TAV} < I_T < 1.5 \pi I_{TAV}$	
I_H	Holding current, max	mA	500	$T_j = 25$ $^{\circ}$ C; $V_D = 12$ V; Gate open	
BLOCKING					
I_{DRM} , I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150	$T_j = T_{j\max}$; $V_D = V_{DRM}$; $V_R = V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/ μ s	200, 320, 500, 1000, 1600, 2000, 2500	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	$V_D = 12$ V; $I_D = 3$ A; Direct gate current
I_{GT}	Gate trigger direct current, max	mA	500 300 150	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.40	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$;	
I_{GD}	Gate non-trigger direct current, min	mA	75.00	Direct gate current	
SWITCHING					
t_{gd}	Delay time, max	μ s	0.90	$T_j = 25$ $^{\circ}$ C; $V_D = 1000$ V; $I_{TM} = I_{TAV}$; $di/dt = 200$ A/ μ s;	
t_{gt}	Turn-on time ²⁾ , max	μ s	2.00, 2.50, 3.20, 4.00	Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ μ s; $di_G/dt = 2$ A/ μ s	
t_q	Turn-off time ³⁾ max	μ s	20.0, 25.0, 32.0, 40.0	$dv_D/dt = 50$ V/ μ s	$T_j = T_{j\max}$; $I_{TM} = I_{TAV}$; $di_R/dt = -10$ A/ μ s; $V_R = 100$ V; $V_D = 0.67 V_{DRM}$
			25.0, 32.0, 40.0, 50.0	$dv_D/dt = 200$ V/ μ s	

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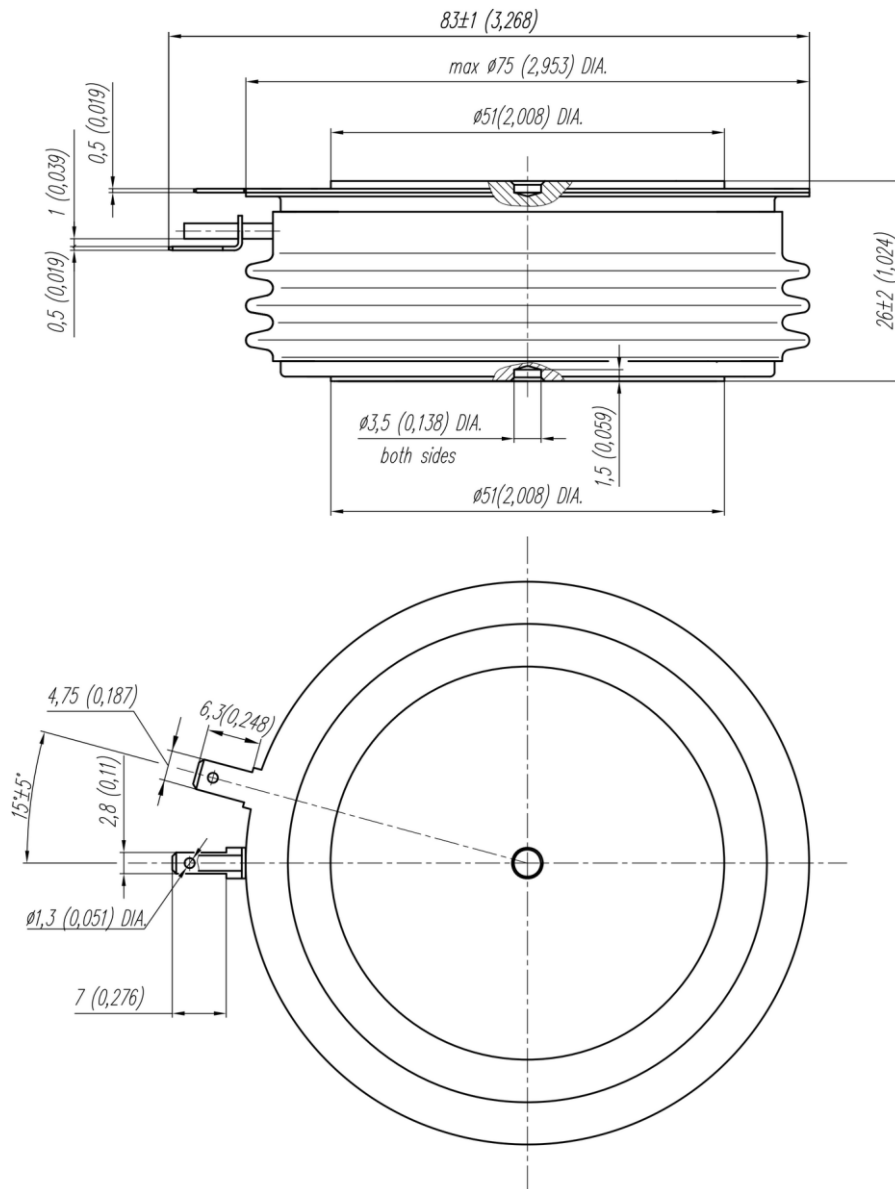
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0210	Direct current	Double side cooled
R_{thjc-A}			0.0462		Anode side cooled
R_{thjc-K}			0.0378		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0040	Direct current	
MECHANICAL					
w	Weight, max	g	550		
D_s	Surface creepage distance	mm (inch)	29.47 (1.160)		
D_a	Air strike distance	mm (inch)	17.50 (0.689)		

PART NUMBERING GUIDE								NOTES										
FDT	56	1000	22	7	3	2												
1	2	3	4	5	6	7		1) Critical rate of rise of off-state voltage										
1. FDT — Fast Disc Thyristor								Symbol of Group		4	5	6	7	8	8.5	9		
2. Element Diameter								$(dv_D/dt)_{crit}$, V/μs		200	320	500	1000	1600	2000	2500		
3. Mean on-state current, A								2) Turn-on time										
4. Voltage code								Symbol of group		5	4	3	2					
5. Critical rate of rise of off-state voltage								t_{gt} , μs		2.00	2.50	3.20	4.00					
6. Group of turn-off time ($dv_D/dt=50$ V/μs)								3) Turn-off time ($dv_D/dt=50$ V/μs)										
7. Group of turn-on time								Symbol of group		6	5	4	3					
								t_{a} , μs		20.0	25.0	32.0	40.0					

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OVERALL DIMENSIONS

Package type: T.D2



All dimensions in millimeters (inches)